

10th International Symposium on Control of Semiconductor Interfaces

International Conference on Silicon Epitaxy International SiGe Technology and Device Meeting

November 10 (Mon.) - 13 (Thu.), 2025

Institute of Science Tokyo, Suzukake Campus, Kanagawa, Japan

<https://icsi.sakura.ne.jp/icsi10/>

The 10th International Symposium on Control of Semiconductor Interfaces (ISCSI-X), the International Conference on Silicon Epitaxy and International SiGe Technology and Device Meeting (ICSI/ISTDM 2025) will be held in Yokohama-shi, Kanagawa, Japan. Aiming for global collaboration dedicated to semiconductor interfaces, ISCSI series first commenced in Karuizawa, Japan, 1993. Continuing the series in 1996, 1999, 2002 in Karuizawa, in 2007 in Hachioji, Japan, in 2013 in Fukuoka, Japan, in 2016, 2022 in Nagoya, Japan, and in 2019 in Sendai, Japan. ISCSI has been established itself as a platform where we discuss research results on semiconductor interfaces, exchange information, and promote them for future semiconductor science and technology.

Previous ICSI conferences were held in 1st: Miyagi Zao, Japan, 1999; 2nd: Strasbourg, France, 2001; 3rd: Santa Fe, USA, 2003; 4th: Awaji Island, Japan, 2005; 5th: Marseille, France, 2007; 6th: Los Angeles, USA, 2009, 7th: Leuven, Belgium, 2011, 8th: Kyushu, Japan, 2013; 9th: Montreal, Canada, 2015. Also, previous ISTDM conferences were in 1st: Nagoya, Japan, 2003; 2nd: Frankfurt (Oder); 3rd: Germany, 2004, 4th: Princeton, USA, 2006; 6th: Hsinchu, Taiwan; 2008, 7th: Stockholm, Sweden; 2010, 8th: Berkeley, USA, 2012; 9th: Singapore, 2014; 10th: Nagoya, Japan, 2016. Then, both meetings have been joined as ISTDM/ICSI, those were held in Potsdam, Germany, 2018; Como, Italy, 2023. We have been continuing these meetings to discuss the group-IV semiconductor engineering technologies through materials science to device applications.

Topic Areas

Thin Film Growth and Characterization

Si, Strained Si, Ge, SiGe(C), GeSn, SiC, Diamond, Silicide, Compound semiconductors, III-nitrides, Oxide semiconductors

High-k insulator, Low-k insulator

Epitaxial growth, CVD, MBE, Selective epitaxy, Atomic layer control, Novel growth technique

Band engineering, Defect engineering, Theory and Simulation, and modeling

Surface and Interface Control

Surface passivation and modification, Surface and interface chemistry

Schottky and ohmic contacts

Atomic scale characterization of surfaces and interfaces

Surface/interface issues in advanced devices

Formation and Characterization of Nanostructures

Nanodots, Nanowires, Superlattice, Self-assembling, Self-organization

Synthesis of low-dimensional materials (2D materials etc.)

Nanoscale characterization, In-situ characterization, Epitaxy equipment technology, Metrology challenges

Process and Device Technology

Impurity doping/diffusion, Dry etching, Microfabrication, Isolation, Heterostructure devices combined with 2D materials,

SOI, SGOI, III-V on Si, Wafer bonding, Virtual substrates and their Manufacturing

CMOS, HBT, BiCMOS, FeRAM, MODFET, SET, RTD, LED, LD, OEIC

Advanced thermal processing, Source/drain & channel engineering, Base/emitter engineering, Fin FET/GAAFET, Semiconductor-superconductor integration, Photonic devices, Quantum technology

Depending on the topics, the accepted papers will be preferentially assigned to ISCSI, ICSI/ISTDM, or Joint sessions.

Submission of Papers

Paper acceptance is based on abstract submission. The work must be original and unpublished. Prospective authors should submit abstract(s) (only in PDF file), two pages in length including all figures and tables, by **July 10th, 2025**, to a submission World Wide Web site (the site information will be announced at the above symposium web site). The two-page abstract must be written in English and typed in an area of 8.5 x 11 inches or A4 size. The first page must be headed by the title of the paper, author(s), affiliation(s), address, telephone number, e-mail address of the corresponding author. The text of the abstract must clearly and concisely state the specific results of the work and its originality. Please refer to the sample abstract (PDF file at the above symposium web site) for detailed format information. An abstract template (Microsoft Word) is available at the above symposium web site, and please follow the instructions for preparation of your abstract(s). Proceedings will be published in a special issue of an academic journal. Detailed information will be announced on the above symposium web site.

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ISCIS-X

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